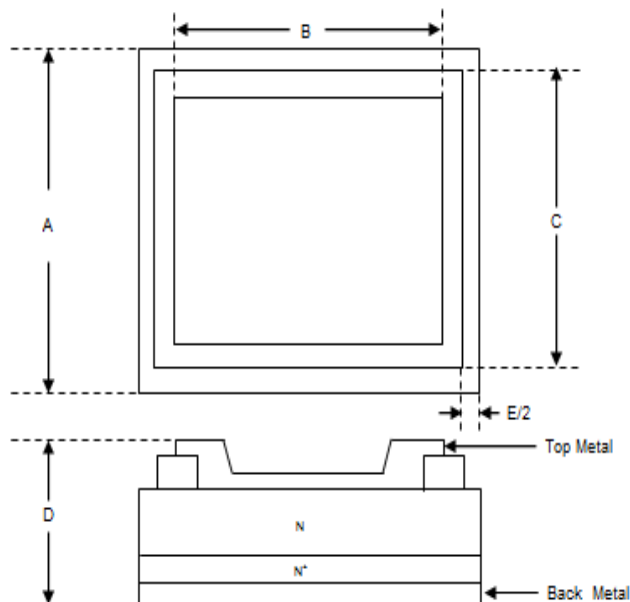


### Planar MOS-Controlled Diode Wafer (PMCD)



| Item                   | Dimensions |      |
|------------------------|------------|------|
|                        | um         | mil  |
| Die Size (A)           | 2540       | 100  |
| Top Metal Pad Size (B) | 2330       | 91.7 |
| Passivation Seal (C)   | 2480       | 97.6 |
| Wafer Thickness (D)    | 260        | 10.2 |
| Scribe Line Width (E)  | 60         | 2.36 |
| Other Informations     |            |      |
| Wafer Size             | 6"         |      |
| Gross Die              | 2460       |      |
| Top Metal              | Ag         |      |
| Back Metal             | Ag         |      |

| Electrical Characteristics @TA=25°C   |           |                           |                     |         |
|---|-----------|---------------------------|---------------------|---------|
| Item  | Symbol    | Spec. Limit               | Die Sort            | Unit    |
| Maximum Repetitive Peak Reverse Voltage<br>@0.3mA   | $V_{RRM}$ | 60                        | 64                  | V       |
| Maximum Average Forward Rectified Current   | $I_O$     | 15                        | -                   | A       |
| Forward Voltage Drop,<br>@ $I_F=2A$<br>@ $I_F=5A$<br>@ $I_F=10A$<br>@ $I_F=15A$                   | $V_F$     | -<br>0.45<br>0.53<br>0.59 | 0.38<br>-<br>-<br>- | V       |
| Maximum Reverse Current at Rated $V_{RRM}$  | $I_R$     | 130                       | 100                 | $\mu A$ |
| Peak Forward Surge Current, 8.3ms Single Half Sine-wave Superimposed on Rated Load (JEDEC Method) | $I_{FSM}$ | 250                       | -                   | A       |
| Operating Temperature Range   | $T_J$     | -50 to +150               | -                   | °C      |
| Storage Temperature Range   | $T_{STG}$ | -50 to +150               | -                   | °C      |